

7.5A SCR: 7.5A系列塑封高壓單向可控硅【器件參數】

無鉛產品提供SGS環保認證，符合歐美RoHS環保指令標準

■ QUICK REFERENCE 【參考特性】

產品型號 Part Number	工業型號 Industry Part No	通態電流均方值 IT(RMS) (A)	斷態重復峰值電壓 VDRM / VRMM (V)	門極觸發電流 IGT (μ A / mA)	封裝外形 Package	包裝方式 Packing	元件標識 Marking
HBTA151-500R	BT151U-500R	7.5 A	500 V	≤ 5 mA	DIP TO-251 I-PAK	TO-251 80Pcs/Tube 4Kpcs/Box 每管80只 每盒4000只 2.1g / Pcs 每枚重量2.1克 每K重2.5千克	
HBTA151-600R	BT151U-600R		600 V				
HBTA151-650R	BT151U-650R		650 V				
HBTA151-800R	BT151U-800R		800 V				

①除TO-251封裝外，還接受可訂製TO-252、TO-220、TO-126封裝，對應工業型號BT151U-C系列
 ②常規電壓以600V規格出貨，高壓規格特殊品種600V以上批量交期6~8周
 ③門極觸發電流 I_{GT} 值可根據客戶要求細分至多個規格，單位mA

■ PINNING: TO-251 (SOT533) 【TO-251直插半塑封即：I-PAK、SOT-533、DPAK-3】【公司產品此規格為特殊生產品種】

Pin 管腳排列	Symbol 對應極性	Description 極性名詞	Description 極性含義	Practicality in Pin Arrange 元件實物與管腳排列說明	Pin Polarity Circuit diagram 腳位與極性 電路符號表示
1	K	Cathode	陰極		1=K 2=A 3=G 4=A=2
2	A	Anode	陽極		
3	G	Gate	門控制極		
4	Tab	Anode	散熱片		

■ ABSOLUTE RATINGS (Limiting Values) 【額定值参数】

SYMBOL 符號表示	Paramenter & Test Conditions 符號含義 及 參數測試條件說明	Value 數值	Unit 單位
$I_{T(RMS)}$	通態電流均方值: On-State RMS Current (Tc=100°C) 100°C Conduction Angles	7.5	A
I_{TSM}	通態浪湧電流: ½周期, 60Hz, 正弦波, 不重複, t=8.3mS Peak Non-Repetitive Surge Current (½ Cycle, Sine Wave, 60Hz, Tj=25°C)	110	
I_{GM}	門極峰值電流 Peak gate current	<2	
I^2t	週期電流平方時間積 I^2t for fusing (t=10mS)	50	
V_{RGM}	門極峰值電壓 Peak gate voltage	<12	V
V_{DRM} / V_{RRM}	斷態重複峰值電壓 Repetitive peak off-state voltages (參見型號說明)	500~1000	
$P_{G(AV)}$	門極平均散耗功率 Average gate power (over any 20 ms period)	0.5	W
P_{GM}	門極平均散耗功率 Peak gate power	5	
T_j	工作結溫 Operating Junction Temperature Range @ Rate VRMM and VDRM	-40 ~ +125	°C
Tstg	貯存溫度 Storage Temperature Range	-40 ~ +150	

■ ELECTRICAL CHARACTERISTICS (Tj=25°C Unless Otherwise Noted) 【電参数】

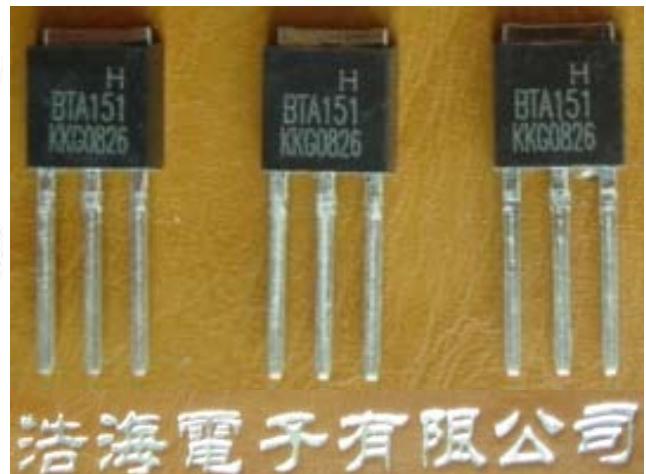
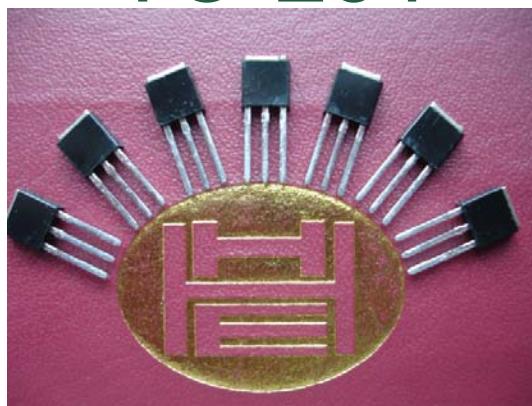
SYMBOL 符號表示	Paramenter & Test Conditions 符號含義 及 參數測試條件說明	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
I_{GT}	門極觸發電流: VD=12V, IT=0.1A	→	2	5	mA
I_H	維持電流: Holding Current (VD=12V, IGT=0.1A)	→	7	16	
I_L	關閉電流: Latching current (VD=12V, IGT=0.1A)	→	10	40	
V_{GT}	門極觸發電壓: VD=12V, IT=0.1A	→	0.6	1.5	V
	門極觸發電壓: VD=VDRM, IT=0.1A, Tj = 125°C	0.25	0.4	→	
V_{TM}	峰值通態電壓: Peak Forward On-State Voltage (IT=23A)	→	1.4	1.75	
dv / dt	斷態臨界電壓上升率: Critical Rate of Rise of Off-State Voltage	→	→	500	V/μs
di / dt	通態臨界電流上升率: Critical Rate of Rise of On-State Current	→	→	50	A/μs
T_{qt}	門極啟動之導通時間: Gate Controlled Turn-on Time	→	2	→	μs
T_q	一周期轉換關斷時間: Circuit Commutated Turn-off Time	→	70	→	
$R_{th(j-c)}$	熱阻-結到外殼: Thermal Resistance-Junction-to-Case	→	→	1.1	
$R_{th(j-a)}$	熱阻-結到環境: Thermal Resistance-Junction-to-Ambient	→	→	60	°C/W

MECHANICAL DATA

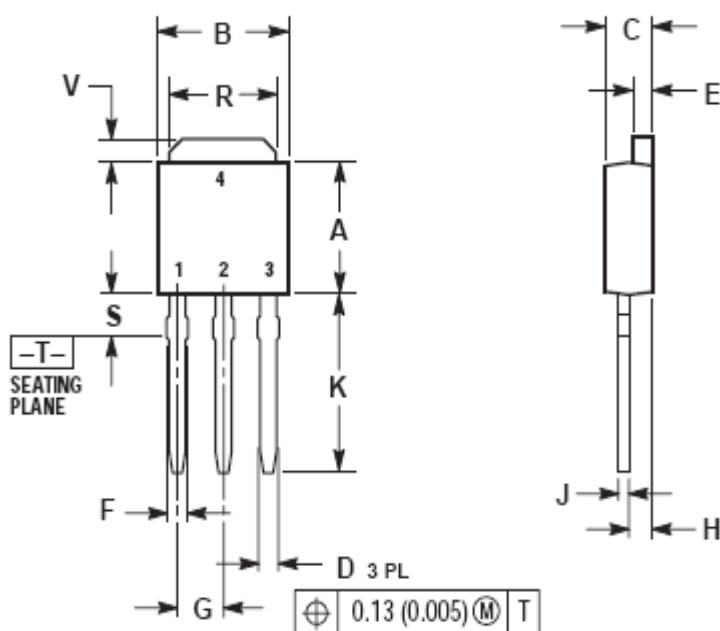
TO-251 封裝尺寸

單位:毫米 mm

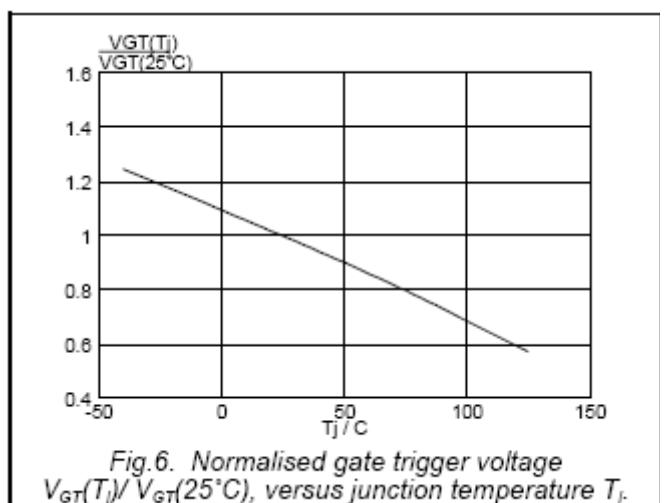
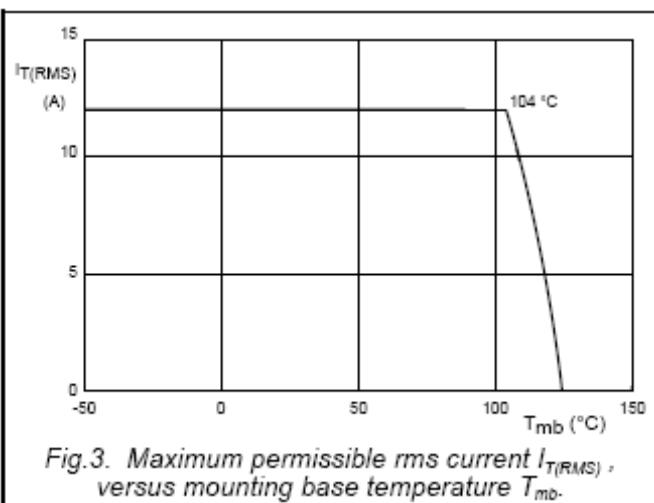
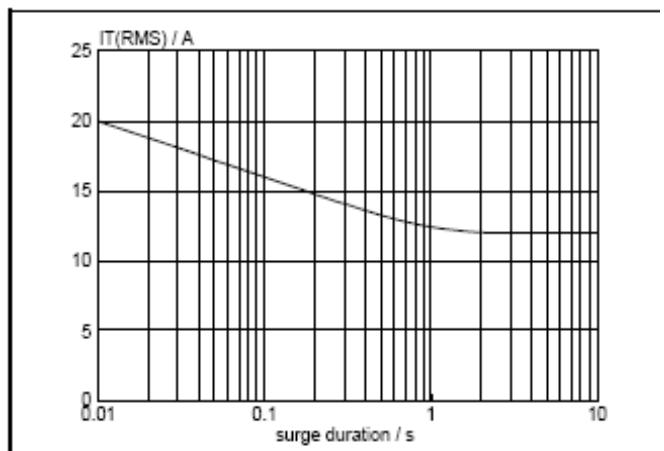
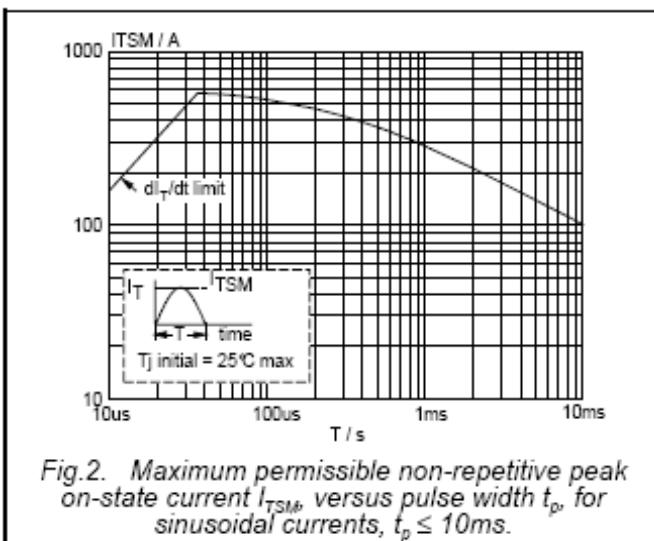
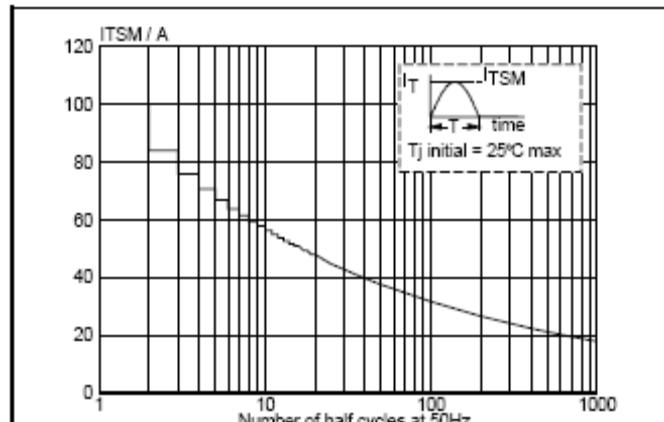
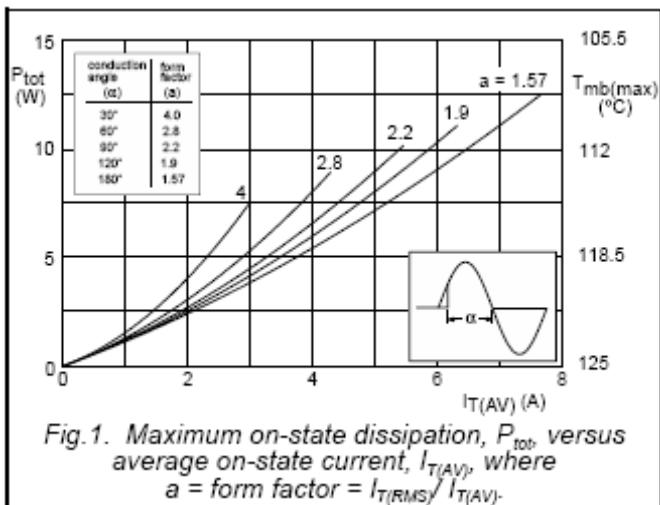
TO-251



元件列印標識說明: **H**: 浩海電子; **BTA151**為型號; **KKG**: 公司品牌; **0826**: 出廠批號為2008年第26週



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1.27



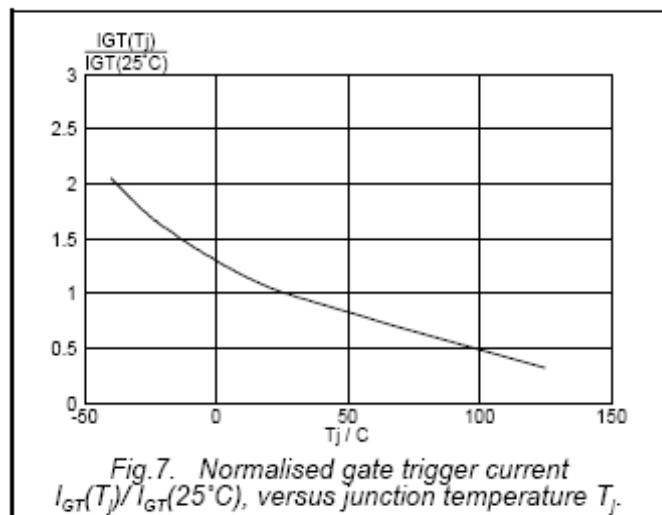


Fig.7. Normalised gate trigger current $I_{GT}(T_j)/I_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

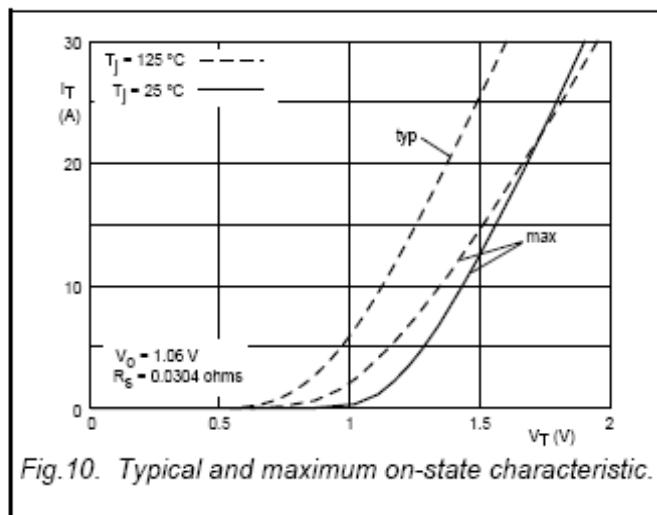


Fig.10. Typical and maximum on-state characteristic.

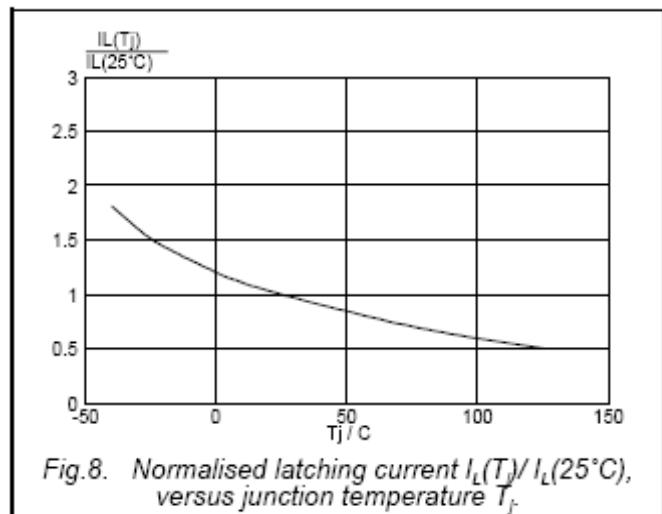


Fig.8. Normalised latching current $I_L(T_j)/I_L(25^\circ\text{C})$, versus junction temperature T_j .

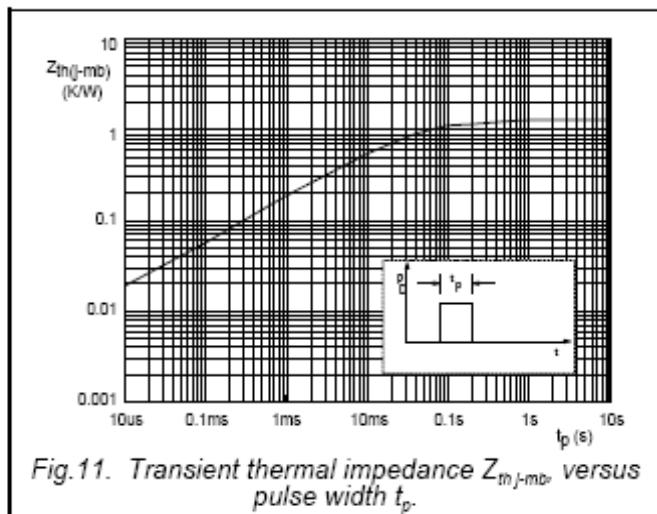


Fig.11. Transient thermal impedance $Z_{th(j-mb)}$ versus pulse width t_p .

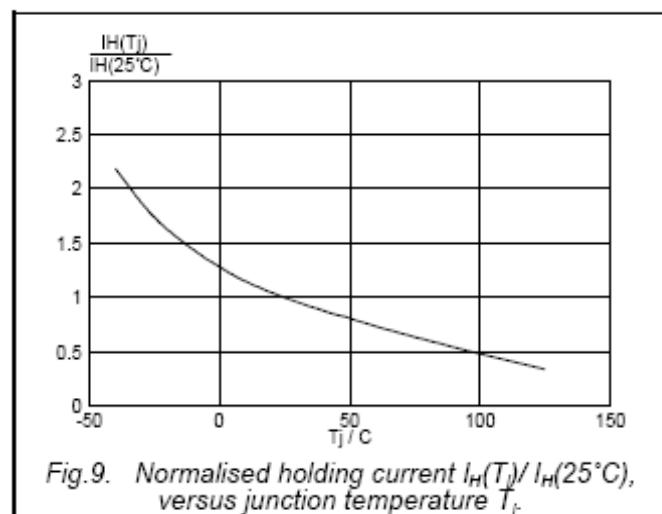


Fig.9. Normalised holding current $I_H(T_j)/I_H(25^\circ\text{C})$, versus junction temperature T_j .

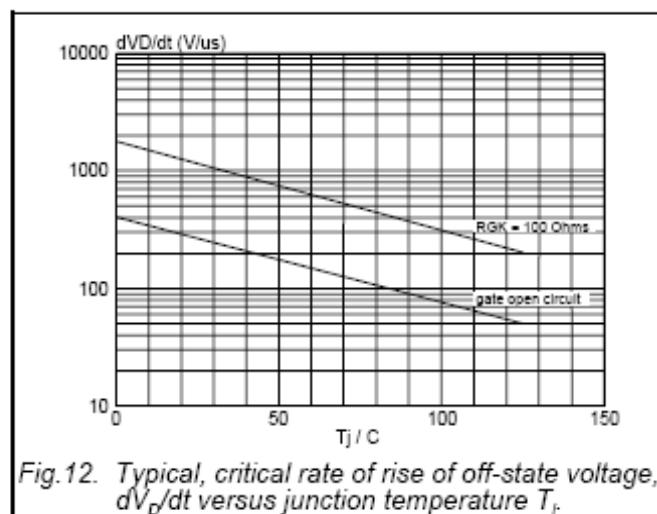


Fig.12. Typical, critical rate of rise of off-state voltage, dV_d/dt versus junction temperature T_j .